



DSS4160T

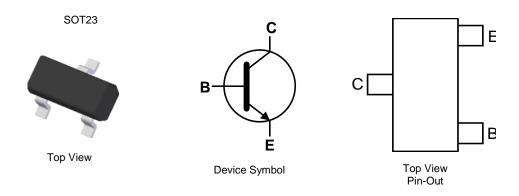
### **60V NPN LOW SATURATION TRANSISTOR IN SOT23**

#### **Features**

- BV<sub>CEO</sub> > 60V
- I<sub>C</sub> = 1A High Continuous Collector Current
- I<sub>CM</sub> = 2A Peak Pulse Current
- R<sub>CE(sat)</sub> = 280mΩ for a Low Equivalent On-Resistance
- Low Saturation Voltage V<sub>CE(sat)</sub> < 280mV @ 1A</li>
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.008 grams (Approximate)



### Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DSS4160T-7	AEC-Q101	ZN9	7	8	3,000
DSS4160TQ-7	Automotive	ZN9	7	8	3,000

#### Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_compliance\_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**

ZN9

SOT23

ZN9 = Product Type Marking Code



### Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	80	V
Collector-Emitter Voltage	V <sub>CEO</sub>	60	V
Emitter-Base Voltage	V <sub>EBO</sub>	5	V
Continuous Collector Current	I <sub>C</sub>	1	Α
Peak Pulse Collector Current	Ісм	2	Α
Base Current	IB	300	mA
Peak Base Current	I <sub>BM</sub>	1	А

# Thermal Characteristics (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P <sub>D</sub>	725	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	172	°C/W
Thermal Resistance, Junction to Leads (Note 7)	$R_{ heta JL}$	79	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

### **ESD Ratings** (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

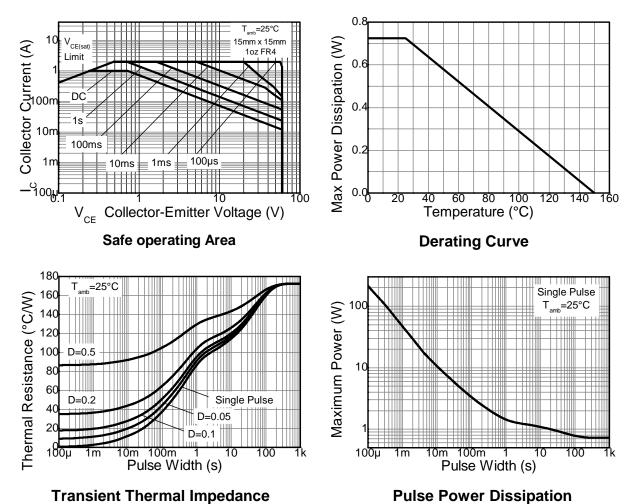
<sup>6.</sup> For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

<sup>7.</sup> Thermal resistance from junction to solder-point (at the end of collector lead).

8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



## **Thermal Characteristics and Derating Information**



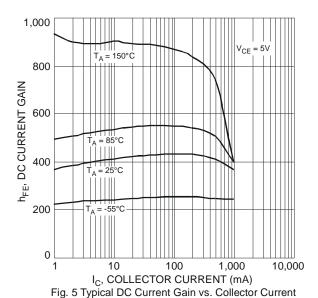


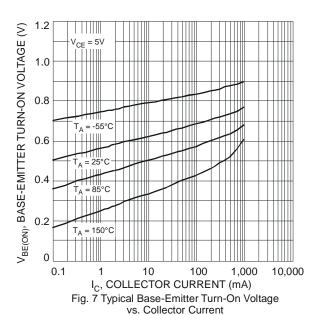
## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

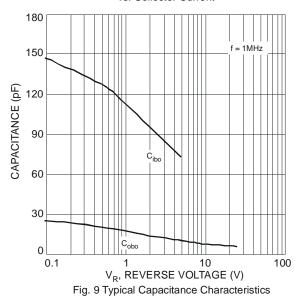
Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions	
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	80	_	_	V	$I_{C} = 100 \mu A$	
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	60	_	_	V	I <sub>C</sub> = 10mA	
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	5	_	_	V	I <sub>E</sub> = 100μA	
Collector-Base Cutoff Current			_	100	nA	V <sub>CB</sub> = 60V, I <sub>E</sub> = 0	
Collector-Base Cutori Current	I <sub>CBO</sub>		_	50	μΑ	V <sub>CB</sub> = 60V, I <sub>E</sub> = 0, T <sub>A</sub> = +150°C	
Collector Cutoff Current	ICES		_	100	nA	V <sub>EB</sub> = 60V, I <sub>BE</sub> = 0	
Emitter-Base Cutoff Current	I <sub>EBO</sub>		_	100	nA	V <sub>EB</sub> = 5V, I <sub>C</sub> = 0	
		250	_	_		$V_{CE} = 5V$ , $I_C = 1mA$	
DC Current Gain (Note 9)	h <sub>FE</sub>	200	_	_	_	V <sub>CE</sub> = 5V, I <sub>C</sub> = 500mA	
		100	_	_		V <sub>CE</sub> = 5V, I <sub>C</sub> = 1A	
		_	_	115		I <sub>C</sub> = 100mA, I <sub>B</sub> = 1mA	
Collector-Emitter Saturation Voltage (Note 9)	V <sub>CE(sat)</sub>	_	_	150	mV	I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA	
			_	280		I <sub>C</sub> = 1A, I <sub>B</sub> = 100mA	
Equivalent On-Resistance	R <sub>CE(sat)</sub>		_	280	mΩ	I <sub>E</sub> = 1A, I <sub>B</sub> = 100mA	
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	_	_	1.1	V	I <sub>C</sub> = 1A, I <sub>B</sub> = 50mA	
Base-Emitter Turn-on Voltage	V <sub>BE(on)</sub>		_	0.9	V	V <sub>CE</sub> = 5V, I <sub>C</sub> = 1A	
Transition Frequency	f <sub>T</sub>	150	_	_	MHz	$V_{CE} = 10V, I_{C} = 50mA,$ f = 100MHz	
Output Capacitance	C <sub>obo</sub>	_	_	10	pF	V <sub>CB</sub> = 10V, f = 1MHz	
Turn-On Time	ton	_	63	_	ns		
Delay Time	t <sub>d</sub>	_	33	_	ns		
Rise Time	t <sub>r</sub>		30	_	ns	$V_{CC} = 10V, I_C = 0.5A,$	
Turn-Off Time	t <sub>off</sub>	_	420	_	ns	$I_{B1} = -I_{B2} = 25mA$	
Storage Time	ts	_	380	_	ns	]	
Fall Time	t <sub>f</sub>	_	40	_	ns		

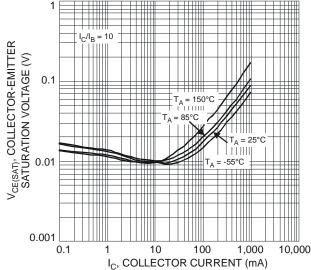
Note: 9. Measured under pulsed conditions. Pulse width  $\leq 300 \mu s$ . Duty cycle  $\leq 2\%$ .



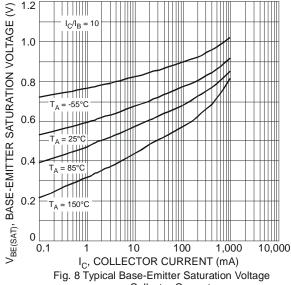








I<sub>C</sub>, COLLECTOR CURRENT (mA)
Fig. 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current



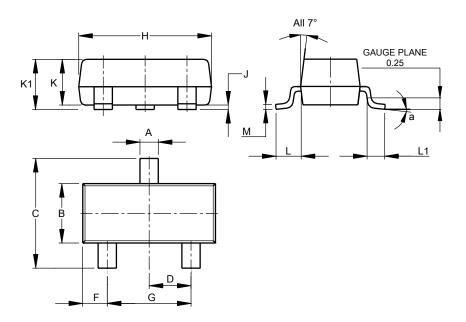
vs. Collector Current



### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23

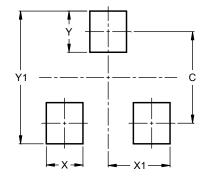


SOT23				
Dim	Min	Max	Тур	
Α	0.37	0.51	0.40	
В	1.20	1.40	1.30	
C	2.30	2.50	2.40	
D	0.89	1.03	0.915	
F	0.45	0.60	0.535	
G	1.78	2.05	1.83	
Η	2.80	3.00	2.90	
7	0.013	0.10	0.05	
K	0.890	1.00	0.975	
K1	0.903	1.10	1.025	
١	0.45	0.61	0.55	
L1	0.25	0.55	0.40	
M	0.085	0.150	0.110	
а	0°	8°		
All Dimensions in mm				

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23



Dimensions	Value (in mm)		
С	2.0		
Х	0.8		
X1	1.35		
Υ	0.9		
Y1	2.9		



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